# Power MOSFET –20V, 49mΩ, –4.5A, Single P-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

#### **Features**

- Low On-Resistance
- 1.5V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

#### **Typical Applications**

- Load Switch
- LCD Drive Switch

#### **SPECIFICATIONS**

#### **ABSOLUTE MAXIMUM RATING** at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-20	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (DC)	ID	-4.5	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	-18	Α
Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm)	PD	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm² × 0.8mm)	$R_{\theta JA}$	125	°C/W

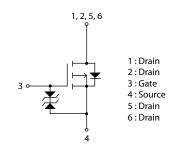


## ON Semiconductor®

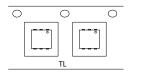
www.onsemi.com

VDSS	R <sub>DS</sub> (on) Max	ID Max	
-20V	49mΩ@ -4.5V		
	64mΩ@ –2.5V	4.54	
	85mΩ@ −1.8V	−4.5A	
	120mΩ@ –1.5V		

# ELECTRICAL CONNECTION P-Channel



## PACKING TYPE : TL MARKING





#### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

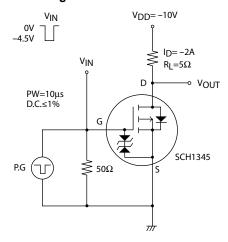
#### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

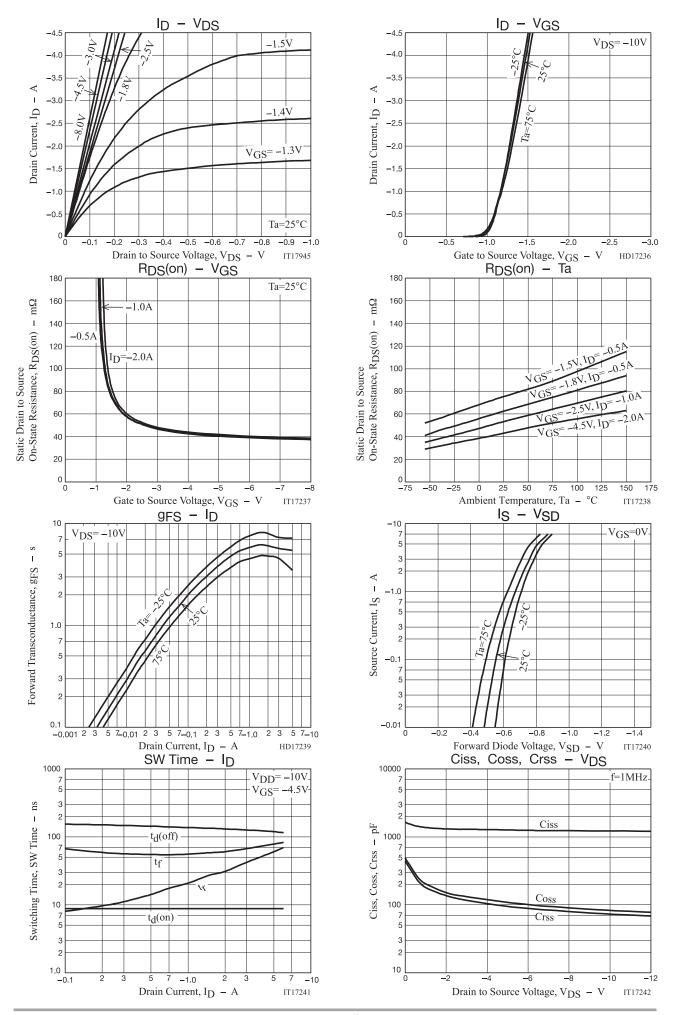
Parameter	Symbol	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.3	V
Forward Transconductance	gFS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A		6		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-2A, V <sub>G</sub> S=-4.5V		42	49	mΩ
Static Drain to Source On-State	R <sub>DS</sub> (on)2	I <sub>D</sub> =-1A, V <sub>G</sub> S=-2.5V		53	64	mΩ
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.5A, V <sub>GS</sub> =-1.8V		65	85	mΩ
	R <sub>DS</sub> (on)4	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-1.5V		74	120	mΩ
Input Capacitance	Ciss			1220		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		82		pF
Reverse Transfer Capacitance	Crss			72		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			8.8		ns
Rise Time	tr	One amonified Test Observit		35		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		123		ns
Fall Time	tf			61		ns
Total Gate Charge	Qg			11		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.5A		1.9		nC
Gate to Drain "Miller" Charge	Qgd			1.9		nC
Forward Diode Voltage	V <sub>SD</sub>	IS=-4.5A, VGS=0V		-0.82	-1.2	V

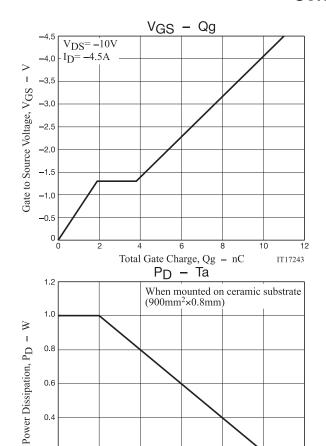
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted.

Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

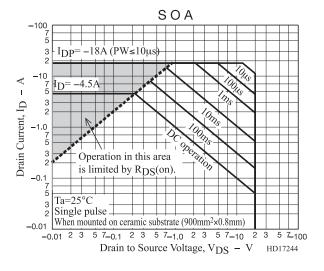
# **Switching Time Test Circuit**

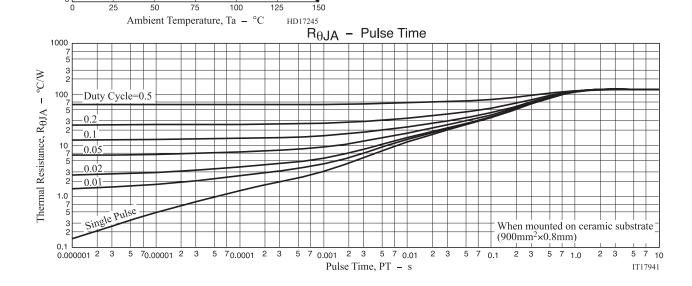






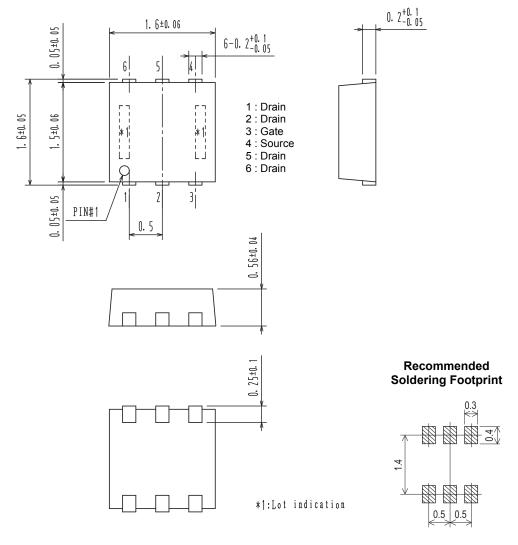
0.2





#### PACKAGE DIMENSIONS

unit: mm SOT-563 / SCH6 CASE 463AB ISSUE O



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)
SCH1345-TL-H	YW	SOT-563 / SCH6 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SCH1345 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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